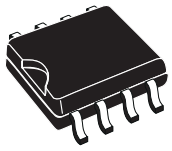
STS3DPF30L

DUAL P - CHANNEL 30V - 0.145Ω - 3A SO-8
STripFET™ POWER MOSFET

PRELIMINARY DATA

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STS3DPF30L	30 V	< 0.16 Ω	3 A

- TYPICAL $R_{DS(on)}$ = 0.145 Ω
- STANDARD OUTLINE FOR EASY AUTOMATED SURFACE MOUNT ASSEMBLY
- LOW THRESHOLD DRIVE



SO-8

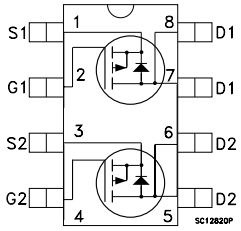
DESCRIPTION

This Power MOSFET is the second generation of STMicroelectronics unique "Single Feature Size™ " strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- BATTERY MANAGMENT IN NOMADIC EQUIPMENT
- POWER MANAGMENT IN CELLULAR PHONES
- DC-DC CONVERTER

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	30	V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	30	V
V_{GS}	Gate-source Voltage	± 20	V
I_D	Drain Current (continuous) at Tc = 25 °C Single Operation Drain Current (continuous) at T_c = 100 °C Single Operation	3 1.9	A A
I_{DM}(•)	Drain Current (pulsed)	12	A
P_{tot}	Total Dissipation at T_c = 25 °C Dual Operation Total Dissipation at T_c = 25 °C Single Operation	2 1.6	W W

(•) Pulse width limited by safe operating area

Note: For the P-CHANNEL MOSFET actual polarity of voltages and current has to be reversed

THERMAL DATA

$R_{thj\text{-}amb}$	*Thermal Resistance Junction-ambient Single Operation	78	$^oC/W$
	Dual Operation	62.5	$^oC/W$
T_j	Maximum Operating Junction Temperature	150	^oC
T_{stg}	Storage Temperature	-55 to 150	^oC

(*) Mounted on FR-4 board ($t \leq 10sec$)

ELECTRICAL CHARACTERISTICS (T_{case} = 25 ^oC unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA V_{GS} = 0	30			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating T_c = 125 ^oC			1 10	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250 µA	1	1.6	2.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V I_D = 1.5 A V_{GS} = 4.5 V I_D = 1.5 A		0.145 0.18	0.16 0.19	Ω Ω
$I_{D(on)}$	On State Drain Current	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max}$ V_{GS} = 10 V	3			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max}$ I_D = 3 A		3		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25 V f = 1 MHz V_{GS} = 0 V		510 170 55		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	V_{DD} = 15 V I_D = 1.5 A R_G = 4.7 Ω V_{GS} = 4.5 V (Resistive Load, see fig. 3)		14.5 37		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 24 V I_D = 3 A V_{GS} = 4.5 V		5.5 1.7 1.8		nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	V_{DD} = 15 V I_D = 1.5 A R_G = 4.7 Ω V_{GS} = 4.5 V (Resistive Load, see fig. 3)		88 23		ns ns

SOURCE DRAIN DIODE

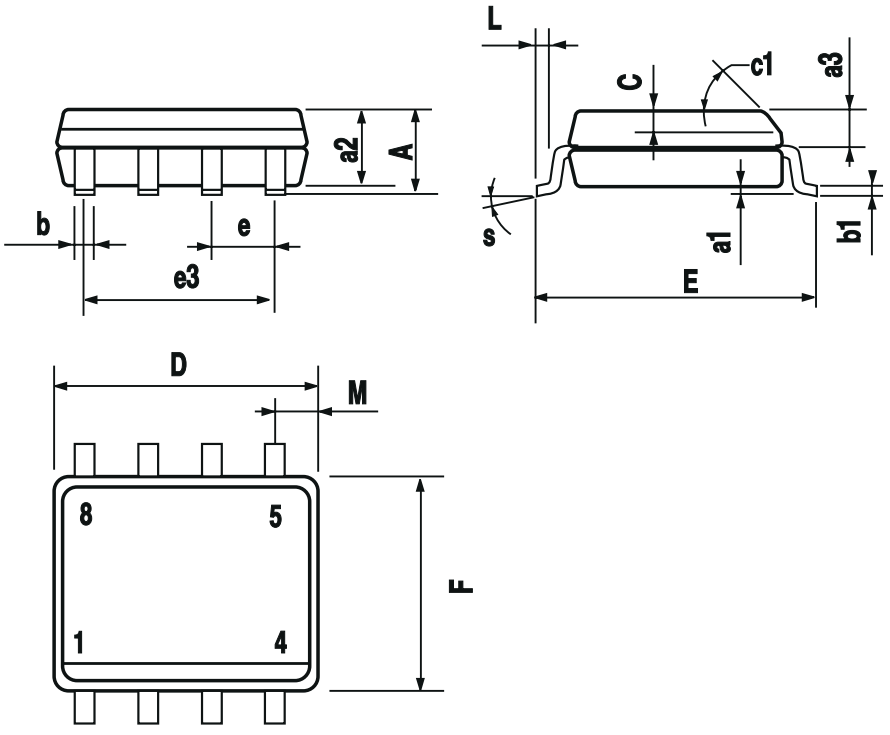
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				3 12	A A
V_{SD} (∗)	Forward On Voltage	I_{SD} =3 A V_{GS} = 0			1.2	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 3 A di/dt = 100 A/µs V_{DD} = 15 V T_j = 150 °C (see test circuit, fig. 5)		T.B.D		ns µC A

(∗) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

(•) Pulse width limited by safe operating area

SO-8 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



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